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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: March 19, 2004 <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	Unassigned 10/2004, 206
				Filing Date	03/19/2004
				First Named Inventor	Tomoya SANUKI
				Group Art Unit	Unassigned 2811
				Examiner Name	Unassigned HUNG JU
Sheet 1 of 1				Attorney Docket Number	016907-1634

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
✓	A1	6,514,885	B1	ONGA ET AL.	02-04-2003	-
✓	A2	5,969,393		NOGUCHI	10-19-1999	-
✓	A3	6,396,113	B1	FUJINAGA ET AL.	05-28-2002	-
✓	A4	6,312,980	B1	ROSTOKER ET AL.	11-06-2001	-

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
✓	A5	G. Scott et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", IEDM Tech. Dig., 1999, pages 827-830.	
✓	A6	K. Rim et al., "Strained Si NMOSFETs for High Performance CMOS Technology", 2001 Symposium on VLSI Technology Digest of Technical Papers, page 59 (2 pages).	
✓	A7	K. Rim et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium on VLSI Technology Digest of Technical Papers, page 98 (2 pages).	

Examiner Signature	HUNG JU	Date Considered	12/20/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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